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- (No author(s) specified) , pp. viii , [PDF \(approx. 58.6KB\)](#)  
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**SIMS analysis of deuterium diffusion in alloy 600: the correlation between fracture mode and deuterium concentration profile** (*Corrosion Science*, Vol: 40, Issue: 1)

- Chene, J.; Lecoester, F.; Brass, A.M.; Noel, D. , pp. 49-60 , [PDF \(approx. 703.1KB\)](#)  
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- **Clayden, J.; Pink, J.H.; Westlund, N.; Wilson, F.X. , pp. 8377-8380 , PDF**  
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